SN74HCT165 8 ビット、パラレルロード・シフト・レジスタ

1 特長

- LSTTL 入力ロジック互換
  - $V_{IL(max)}$ = 0.8V、$V_{IH(min)}$ = 2V
- CMOS 入力ロジック互換
  - $I_I \leq 1\mu A$ (V_{OL}、V_{OH})
- 4.5V～5.5V で動作
- 最大 10 個の LSTTL 負荷ファンアウトに対応
- 直接オーバーライディング・ロード (データ) 入力
- ゲート付きクロック入力
- 拡張周囲温度範囲:–40℃～+125℃、T_A

2 アプリケーション

- マイクロコントローラの入力数拡張

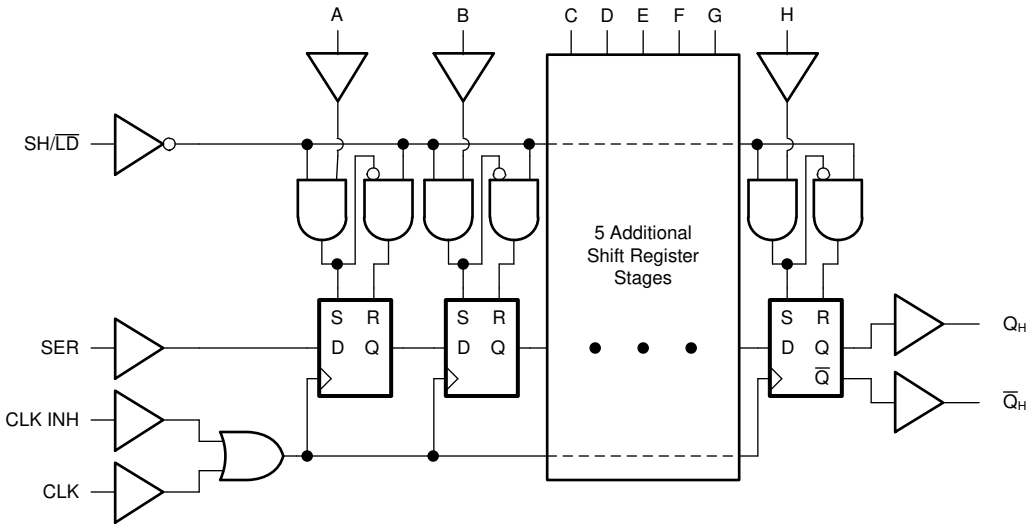
3 概要

SN74HCT165 は、を備えたパラレルまたはシリアル入力、シリアル出力、8 ビット・シフト・レジスタです。各段のパラレル入力へのアクセスは、8 つの個別の直接データ (A～H) 入力によって提供されます。このデータ入力は、シフト / ロード (SH/$\overline{LD}$) 入力が LOW レベルのときイネーブルされます。SN74HCT165 は、クロック禁止 (CLK INH) 機能および相補シリアル ($\overline{Q}_H$) 出力も備えています。

製品情報

部品番号	パッケージ(1)	本体サイズ (公称)
SN74HCT165PW	TSSOP (16)	5.00mm × 4.40mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



論理図 (正論理)

Table of Contents

4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision * (October 2021) to Revision A (December 2021)	Page
• データシートのステータスを事前情報から*量産データに更新*	1

5 Pin Configuration and Functions

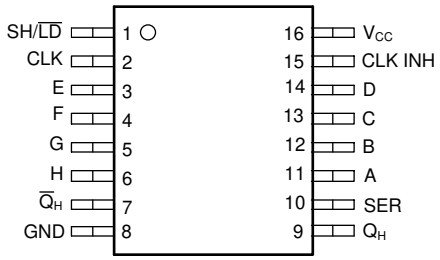


図 5-1. PW Package
16-Pin TSSOP
Top View

表 5-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NAME	NO.		
SH/$\overline{LD}$	1	I	Enable shifting when input is high, load data when input is low
CLK	2	I	Clock, rising edge triggered
E	3	I	Parallel input E
F	4	I	Parallel input F
G	5	I	Parallel input G
H	6	I	Parallel input H
$\overline{Q}_H$	7	O	Inverted serial output
GND	8	—	Ground
Q_H	9	O	Serial output
SER	10	I	Serial input
A	11	I	Parallel input A
B	12	I	Parallel input B
C	13	I	Parallel input C
D	14	I	Parallel input D
CLK INH	15	I	Clock inhibit input
V_{CC}	16	—	Positive supply

(1) Signal Types: I = Input, O = Output, I/O = Input or Output.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	7	V
I_{IK}	Input clamp current(2)	$V_I < 0$ or $V_I > V_{CC} + 0.5$ V	–20	20	mA
I_{OK}	Output clamp current(2)	$V_O < 0$ or $V_O > V_{CC} + 0.5$ V	–20	20	mA
I_O	Continuous output current	$V_O = 0$ to V_{CC}	–35	35	mA
I_{CC}	Continuous output current through V_{CC} or GND		–70	70	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±4000	V
		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002(2)	±1500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		4.5	5	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 4.5 V to 5.5V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 4.5 V to 5.5V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
$\Delta t/\Delta v$	Input transition rise and fall rate	V_{CC} = 4.5 V to 5.5V			500	ns/V
T_A	Ambient temperature		–40		125	°C

6.4 Thermal Information

THERMAL METRIC(1)		SN74HCT165 PW (TSSOP) 16 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	131.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	69.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	76.5	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	20.9	°C/W
Y_{JB}	Junction-to-board characterization parameter	76.1	°C/W

6.4 Thermal Information (continued)

THERMAL METRIC[1]		SN74HCT165 PW (TSSOP) 16 PINS	UNIT
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A = 25°C			-40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	High-level output voltage	V_I = V_{IH} or V_{IL}	I_{OH} = -20 uA, V_{CC} = 4.5 V	4.4			4.4			V
			I_{OH} = -4 mA, V_{CC} = 4.5 V	3.98			3.84			V
V_{OL}	Low-level output voltage	V_I = V_{IH} or V_{IL}	I_{OL} = 20 uA, V_{CC} = 4.5 V			0.1			0.1	V
			I_{OL} = 4 mA, V_{CC} = 4.5 V			0.26			0.33	V
I_I	Input leakage current	V_I = V_{CC} or 0	V_{CC} = 5.5 V			±100			±1000	nA
I_{OZ}	Off-State (High-Impedance State) Output Current	V_O = V_{CC} or 0, Q_A-Q_H	V_{CC} = 5.5 V			±0.5			±5	µA
I_{CC}	Supply current	V_I = V_{CC} or 0, I_O = 0	V_{CC} = 5.5 V			8			80	µA
ΔI_{CC}	Additional Quiescent Device Current Per Input Pin	V_I = V_{CC} - 2.1V	V_{CC} = 4.5V to 5.5V			126.2			157.5	µA
		V_I = 0.5 V or 2.4V	V_{CC} = 5.5V			2.4			2.9	mA
C_i	Input capacitance	V_{CC} = 4.5V to 5.5V	V_{CC} = 4.5V to 5.5V			10				pF
C_O	Output capacitance	V_{CC} = 4.5V to 5.5V	V_{CC} = 4.5V to 5.5V			20				pF
C_{pd}	Power dissipation capacitance per gate	No load				50				pF

6.6 Timing Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		CONDITION	V_{CC}	T_A = 25°C		-40°C to 125°C		UNIT
				MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		4.5 V		31		25	MHz
t_w	Pulse duration	SH/$\overline{LD}$ low	4.5 V	20		25		ns
			5.5 V	20		25		
		CLK high or low	4.5 V	18		23		
			5.5 V	18		23		

6.6 Timing Characteristics (continued)

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		CONDITION	V_{CC}	T_A = 25°C		-40°C to 125°C		UNIT
				MIN	MAX	MIN	MAX	
t_{su}	Setup time	SH/$\overline{LD}$ high before CLK ↑	4.5 V	20		25		ns
			5.5 V	20		25		
		SER before CLK ↑	4.5 V	20		25		
			5.5 V	20		25		
		CLK INH low before CLK ↑	4.5 V	20		25		
			5.5 V	20		25		
		CLK INH high before CLK ↑	4.5 V	20		25		
			5.5 V	20		25		
		Data before SH/$\overline{LD}$ ↓	4.5 V	20		25		
			5.5 V	20		25		
t_h	Hold time	Ser data after CLK ↑ or CLK INH ↑	4.5 V	7		9		ns
			5.5 V	7		9		
		PAR data after SH/$\overline{LD}$ ↓	4.5 V	7		9		
			5.5 V	7		9		

6.7 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		FROM (INPUT)	TO (OUTPUT)	V_{CC}	T_A = 25°C			-40°C to 125°C			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
f_{max}				4.5 V	31			25			MHz
t_{pd}	Propagation delay	SH/$\overline{LD}$	Q_H or Q_H	4.5 V			40			60	ns
				5.5 V			40			60	
		CLK	Q_H or Q_H	4.5 V			40			60	
				5.5 V			40			60	
		H	Q_H or Q_H	4.5 V			35			53	
				5.5 V			35			53	
t_t	Transition-time		Any output	4.5 V			12			15	ns
			Any output	5.5 V			14			17	

6.8 Typical Characteristics

T_A = 25°C

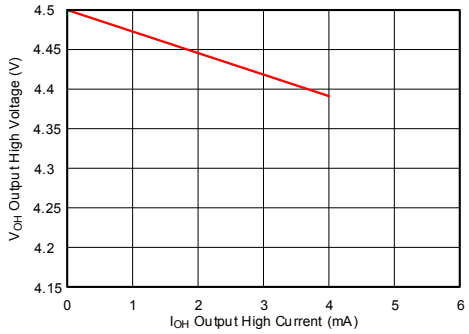


図 6-1. Typical Output Voltage in the High State (V_{OH})

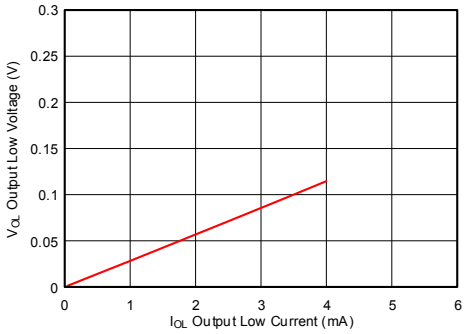


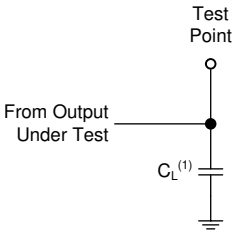
図 6-2. Typical Output Voltage in the Low State (V_{OL})

7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_t < 6 ns.

For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



(1) C_L includes probe and test-fixture capacitance.

図 7-1. Load Circuit for Push-Pull Outputs

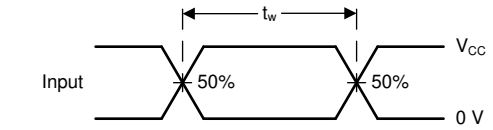


図 7-2. Voltage Waveforms, Pulse Duration

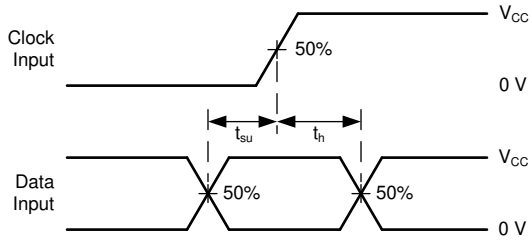
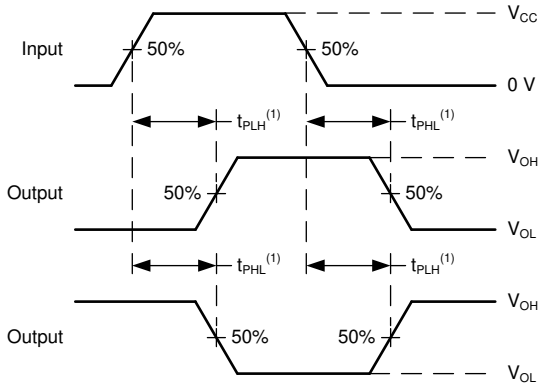
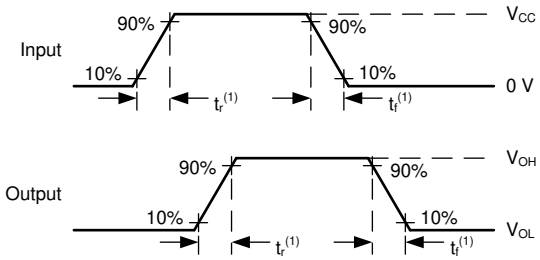


図 7-3. Voltage Waveforms, Setup and Hold Times



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd}.

図 7-4. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t.

図 7-5. Voltage Waveforms, Input and Output Transition Times

8 Detailed Description

8.1 Overview

The SN74HCT165 is a parallel- or serial-in, serial-out 8-bit shift register.

This device has two modes of operation: load data, and shift data.

When the shift or load (SH/$\overline{LD}$) input is held in the low state, the internal registers are loaded with data from the eight lettered inputs (A-H). This operation is asynchronous. In this state, the output (Q) will have the same state as the input H, while the inverted output ($\overline{Q}$) will have the opposite state.

When the shift or load (SH/$\overline{LD}$) input is held in the high state, the internal registers hold their current state until a clock pulse is received. On the rising edge of the clock (CLK) input, data from the serial input will be loaded into the first register, and the data in the internal registers will be shifted by one place. The last register will lose its value. The output (Q) will always be in the same state as the last register, and the inverted output ($\overline{Q}$) will have the opposite state. The clock inhibit (CLK INH) input can be held high to prevent clock pulses from being detected. CLK and CLK INH are interchangable inputs.

8.2 Functional Block Diagram

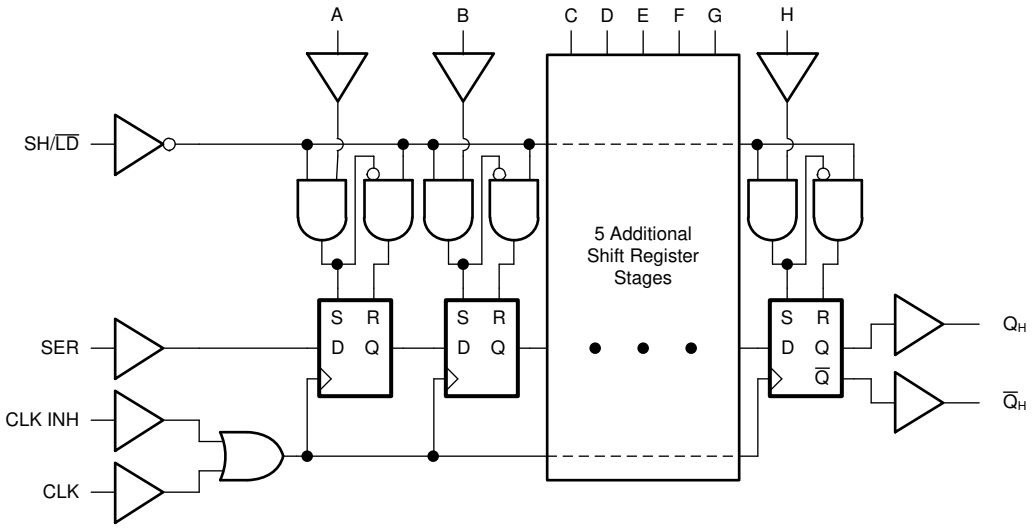


図 8-1. Logic Diagram (Positive Logic) for SN74HCT165

8.3 Feature Description

8.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

8.3.2 TTL-Compatible CMOS Inputs

This device includes TTL-compatible CMOS inputs. These inputs are specifically designed to interface with TTL logic devices by having a reduced input voltage threshold.

TTL-compatible CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law (R = V ÷ I).

TTL-compatible CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in the *Implications of Slow or Floating CMOS Inputs* application report.

Do not leave TTL-compatible CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; however, a 10-kΩ resistor is recommended and will typically meet all requirements.

8.3.3 Latching Logic

This device includes latching logic circuitry. Latching circuits commonly include D-type latches and D-type flip-flops, but include all logic circuits that act as volatile memory.

When the device is powered on, the state of each latch is unknown. There is no default state for each latch at start-up.

The output state of each latching logic circuit only remains stable as long as power is applied to the device within the supply voltage range specified in the *Recommended Operating Conditions* table.

8.3.4 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in 図 8-2.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

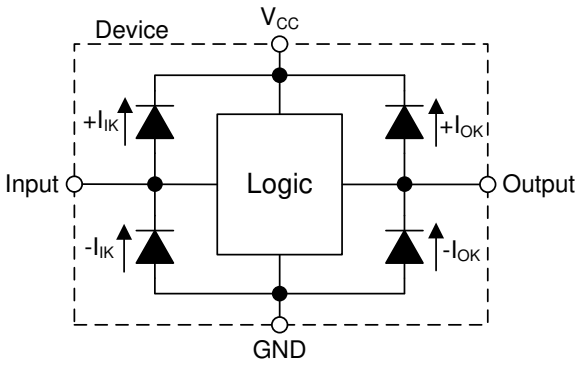


図 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

The Operating Mode Table and the Output Function Table list the functional modes of the SN74HCT165.

表 8-1. Operating Mode Table

INPUTS(1)			FUNCTION
SH/$\overline{LD}$	CLK	CLK INH	
L	X	X	Parallel load
H	H	X	No change
H	X	H	No change
H	L	↑	Shift(2)
H	↑	L	Shift(2)

(1) H = High Voltage Level, L = Low Voltage Level, X = Do not care, ↑ = Low to High transition.
(2) Shift : Content of each internal register shifts towards serial output Q_H. Data at SER is shifted into the first register.

表 8-2. Output Function Table

INTERNAL REGISTERS(1) (2)		OUTPUTS(2)	
A — G	H	Q	$\overline{Q}$
X	L	L	H
X	H	H	L

(1) Internal registers refer to the shift registers inside the device. These values are set by either loading data from the parallel inputs, or by clocking data in from the serial input.
(2) H = High Voltage Level, L = Low Voltage Level, X = Do not care.

9 Application and Implementation

Note

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

9.1 Application Information

The SN74HCT165 is a parallel-input shift register, which can be used to reduce the number of required inputs on a system controller very significantly in some applications. Parallel data is loaded into the shift register, then the stored data can be loaded into a serial input of the system controller by clocking the shift register.

Multiple shift registers can be cascaded to provide more data inputs while still only using a single serial input to the system controller. This process is primarily limited by the required data input rate and timing characteristics of the selected shift register, as defined in the *Timing Charactestics* and *Switching Charactestics* tables.

An example block diagram is shown for using a single shift register in the *Typical Application Block Diagram* below.

9.2 Typical Application

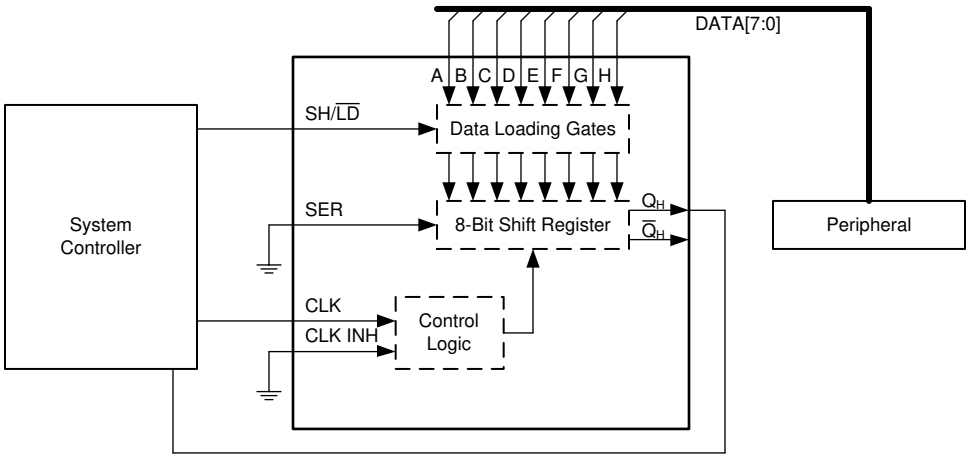


図 9-1. Typical Application Block Diagram

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HCT165 plus the maximum static supply current, I_{CC}, listed in *Electrical Characteristics* and any transient current required for switching. The logic device can only source as much current as is provided by the positive supply source. Be sure not to exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HCT165 plus the maximum supply current, I_{CC}, listed in *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current as can be sunk into its ground connection. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74HCT165 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 50 pF.

The SN74HCT165 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL}. When outputting in the high state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in the *CMOS Power Consumption and Cpd Calculation* application report.

Thermal increase can be calculated using the information provided in the *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices* application report.

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HCT165, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-kΩ resistor value is often used due to these factors.

The SN74HCT165 has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to *Feature Description* section for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCT165 to the receiving device(s).
3. Ensure the resistive load at the output is larger than (V_{CC} / $I_{O(max)}$) Ω. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation.

9.2.3 Application Curve

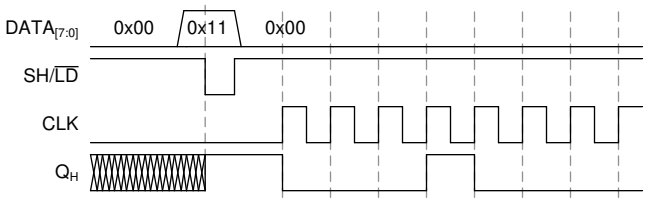


図 9-2. Application Timing Diagram

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1-µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

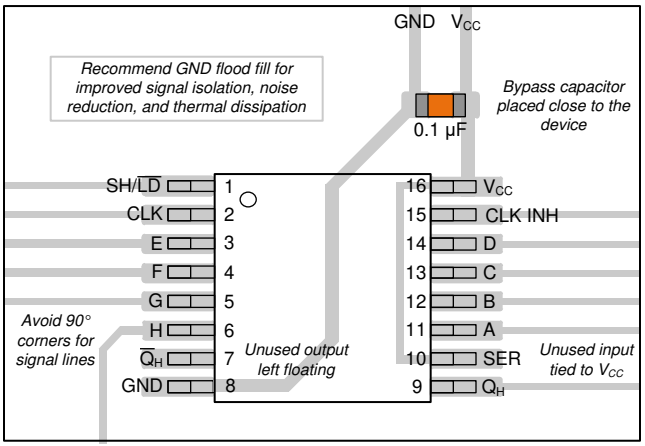


図 11-1. Example Layout for the SN74HCT165 in the PW Package

12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *HCMOS Design Considerations* application report
- Texas Instruments, *CMOS Power Consumption and C_{pd} Calculation* application report
- Texas Instruments, *Designing With Logic* application report

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 サポート・リソース

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12.4 Trademarks

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12.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary — This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74HCT165PWR	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	HT165
SN74HCT165PWR.A	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HT165

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

OTHER QUALIFIED VERSIONS OF SN74HCT165 :

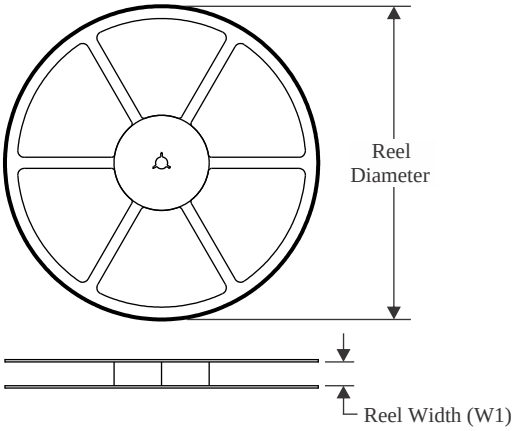
- Automotive : SN74HCT165-Q1

NOTE: Qualified Version Definitions:

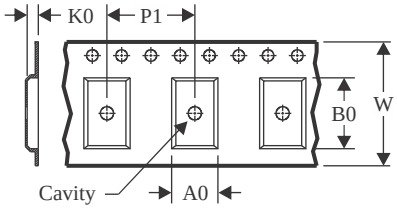
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

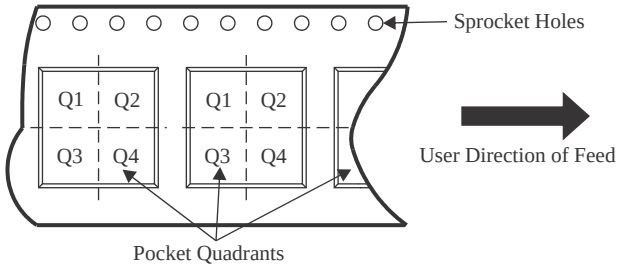


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

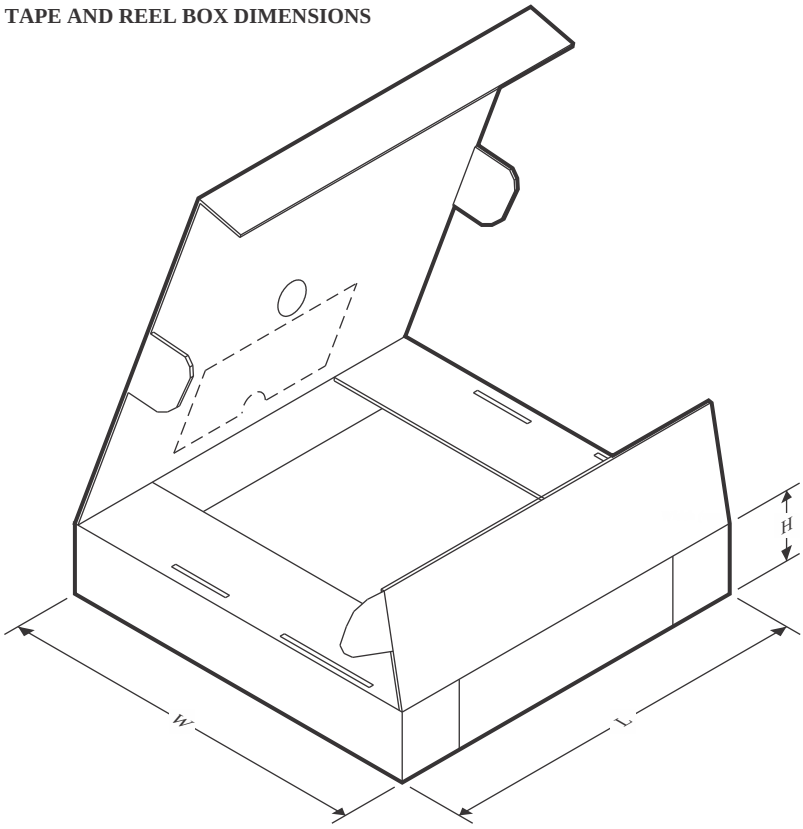
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCT165PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

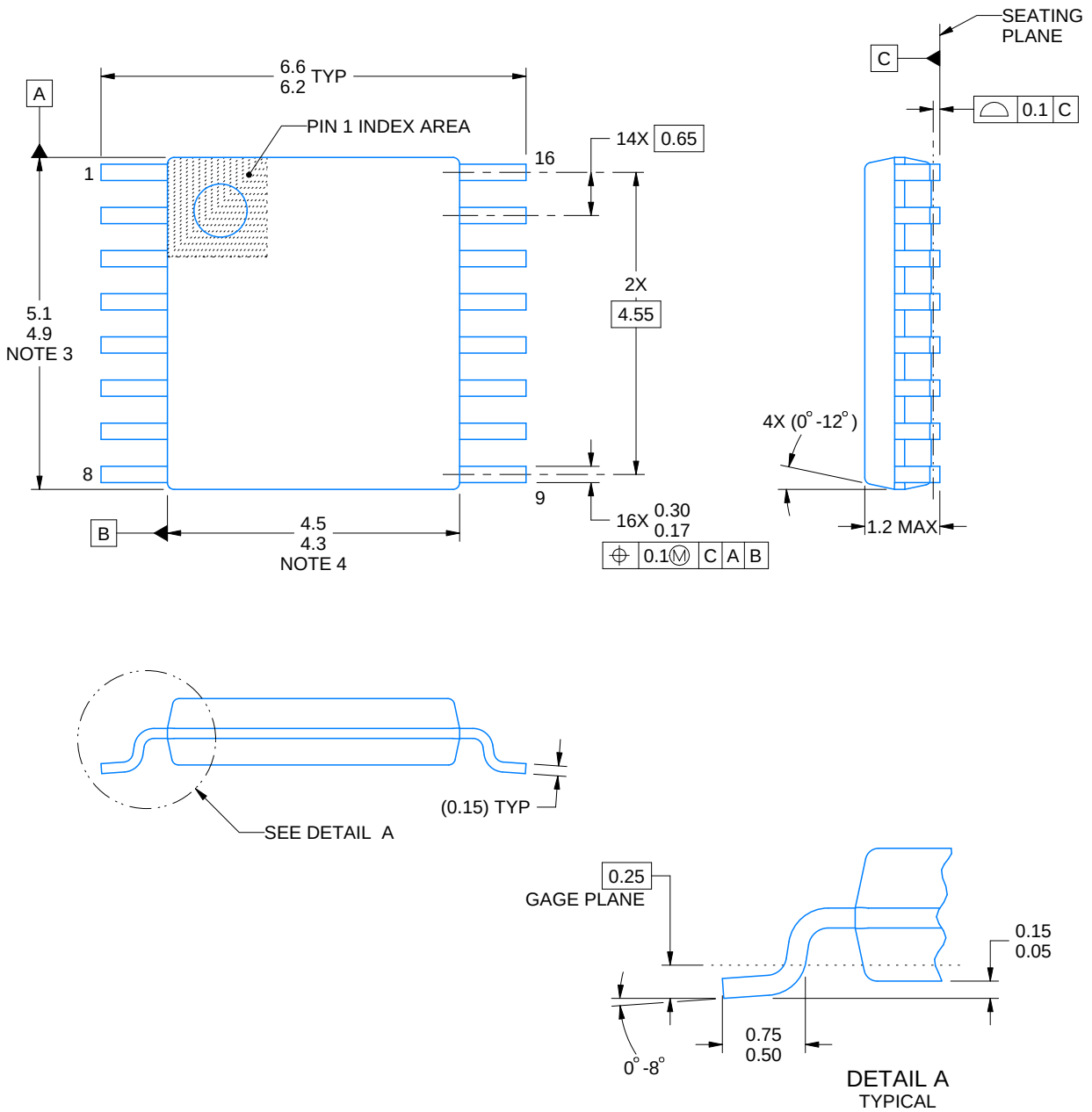
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCT165PWR	TSSOP	PW	16	2000	356.0	356.0	35.0

PACKAGE OUTLINE

PW0016A

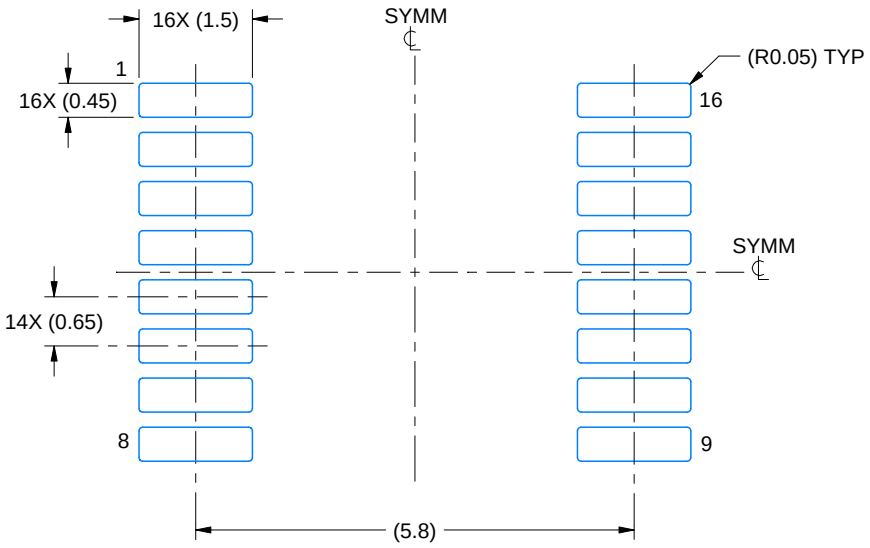
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



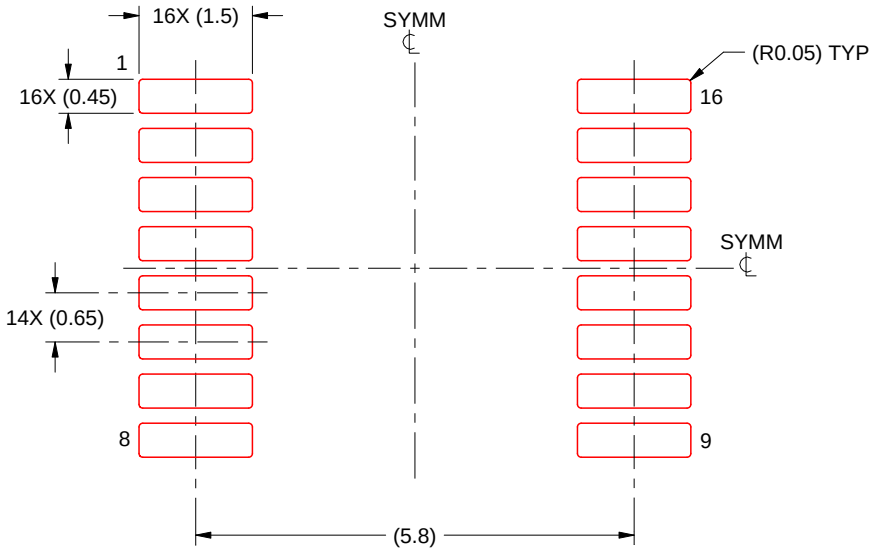
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

SOLDER MASK DETAILS

4220204/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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最終更新日：2025 年 10 月